

## ABSTRACT OF THE DISCLOSURE

Arrangements are provided to effectively prevent wire disconnection generated due to an increase of heat applied to a semiconductor integrated circuit device. The semiconductor integrated circuit device is structured such that a metal layer containing a Pd layer is provided in a portion to which a connecting member having a conductivity is connected, and an alloy layer having a melting point higher than that of an Sn-Pb eutectic solder and containing no Pb as a main composing metal is provided outside a portion molded by a resin. Further, a metal layer in which a thickness in a portion to which the connecting member having the conductivity is adhered is equal to or more than 10  $\mu\text{m}$  is provided in the connecting member.